

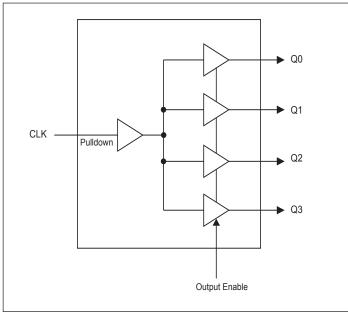


### Low Skew 1 to 4 Clock Buffer

### **Features**

- → Low skew outputs (250 ps)
- → Low power CMOS technology
- → Operating voltages of 1.5V to 3.3V
- → Output enable pin tri-states outputs
- → 3.6V tolerant input clock
- ➔ Industrial temperature ranges
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) →
- Halogen- and Antimony-Free. "Green" Device (Note 3) •
- For automotive applications requiring specific change control • (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/guality/product-definitions/
- → Packaging (Pb-free & Green): 8-pin SOIC (W)

# **Block Diagram**



#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

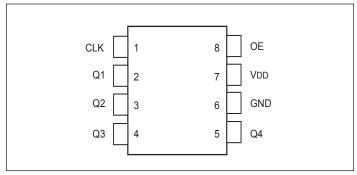
# Description

The PI6C49X0204C is a low skew, single input to four output, clock buffer. The device is perfect for fanning out multiple clock outputs.





# **Pin Configuration**



# **Pin Descriptions**

Pin#	Pin Name	Туре	Pin Description
1	CLK	Input	Clock Input. 3.3V tolerant input. Internal 51k $\Omega$ pull down resistor.
2	Q1	Output	Clock Output 1.
3	Q2	Output	Clock Output 2.
4	Q3	Output	Clock Output 3.
5	Q4	Output	Clock Output 4.
6	GND	Power	Connect to ground.
7	VDD	Power	Connect to 1.5V, 1.8V, 2.5V or 3.3V.
8	OE	Input	Output Enable. Tri-states outputs when low. Internal 125K $\Omega$ pull up resistor. Default on

# **External Components**

A minimum number of external components are required for proper operation. A decoupling capacitor of 0.01 µF should be connected between VDD on pin 7 and GND on pin 6, as close to the device as possible. A 33  $\Omega$  series terminating resistor may be used on each clock output if the trace is longer than 1 inch.





## **Maximum Ratings**

Supply Voltage, VDD 4.6V	No
Output Enable and All Outputs0.5V to VDD+0.5V	Sti to
CLK0.5V to 3.6V (VDD > 0V)	or
Junction Temperature Max. 125°C	tic Ex
Storage Temperature	od
ESD Protection (HBM)2000V	tee

lote:

tresses above the ratings listed below can cause permanent damage the PI6C49X0204C. Functional operation of the device at these r any other conditions above those indicated in the operational secons of the specifications is not implied.

xposure to absolute maximum rating conditions for extended perids can affect product reliability. Electrical parameters are guaraneed only over the recommended operating temperature range.

### **Recommended Operation Conditions**

Parameter	Min.	Тур.	Max.	Units
Ambient Operating Temperature (industrial)	-40		+85	°C
Power Supply Voltage (measured in respect to GND)	+1.425		+3.6	V

### **DC ELECTRICAL CHARACTERISTICS**

VDD=1.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VDD	Operating Voltage		1.425	1.5	1.575	V
V <sub>IH</sub>	Input High Voltage	CLK <sup>(1)</sup>	1.17		3.6	V
V <sub>IL</sub>	Input Low Voltage	CLK <sup>(1)</sup>			0.575	V
I <sub>IH</sub>	Input High Current	CLK <sup>(1)</sup>			40	μΑ
I	Input Low Current	CLK <sup>(1)</sup>			1	μΑ
I <sub>IH</sub>	Input High Current	OE <sup>(1)</sup>			1	μΑ
I	Input Low Current	OE <sup>(1)</sup>			40	μΑ
V <sub>OH</sub>	Output High Voltage	$I_{OH} = -6mA$	0.95			V
V <sub>ol</sub>	Output Low Voltage	$I_{OL} = 6mA$			0.45	V
IDD	Operating Supply Current	No load, 133 MHz			9	mA
Z <sub>o</sub>	Nominal Output Impedance			20		Ω
C <sub>IN</sub>	Input Capacitance	CLK, OE pin		5		pF
I <sub>os</sub>	Short Circuit Current			±12		mA

Notes: 1. Nominal switching threshold is VDD/2





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VDD	Operating Voltage		1.71	1.8	1.89	V
V <sub>IH</sub>	Input High Voltage	CLK <sup>(1)</sup>	1.7		3.6	V
V <sub>IL</sub>	Input Low Voltage	CLK <sup>(1)</sup>			0.6	V
I	Input High Current	CLK <sup>(1)</sup>			50	μΑ
I	Input Low Current	CLK <sup>(1)</sup>			1	μΑ
I <sub>IH</sub>	Input High Current	OE <sup>(1)</sup>			1	μΑ
I	Input Low Current	OE <sup>(1)</sup>			50	μΑ
V <sub>oh</sub>	Output High Voltage	I <sub>OH</sub> = -8mA	1.4			V
V <sub>ol</sub>	Output Low Voltage	$I_{OL} = 8mA$			0.4	V
IDD	Operating Supply Current	No load, 133 MHz			11	mA
Zo	Nominal Output Impedance			20		Ω
C <sub>IN</sub>	Input Capacitance	CLK, OE pin		5		pF
I <sub>os</sub>	Short Circuit Current			±20		mA

#### **VDD=1.8 V \pm5%**, Ambient temperature -40 to +85° C, unless stated otherwise

Notes: 1. Nominal switching threshold is VDD/2

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VDD	Operating Voltage		2.375	2.5	2.625	V
V <sub>IH</sub>	Input High Voltage	CLK <sup>(1)</sup>	1.7		3.6	V
V <sub>IL</sub>	Input Low Voltage	CLK <sup>(1)</sup>			0.7	V
I <sub>IH</sub>	Input High Current	CLK <sup>(1)</sup>			60	μΑ
I <sub>IL</sub>	Input Low Current	CLK <sup>(1)</sup>			3	μΑ
I <sub>IH</sub>	Input High Current	OE <sup>(1)</sup>			3	μΑ
$I_{IL}$	Input Low Current	OE <sup>(1)</sup>			60	μΑ
V <sub>oh</sub>	Output High Voltage	$I_{OH} = -8mA$	2			V
V <sub>ol</sub>	Output Low Voltage	$I_{OL} = 8mA$			0.4	V
IDD	Operating Supply Current	No load, 133 MHz			15	mA
Zo	Nominal Output Impedance			20		Ω
C <sub>IN</sub>	Input Capacitance	CLK, OE pin		5		pF
I <sub>os</sub>	Short Circuit Current			±50		mA

VDD=2.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Notes: 1. Nominal switching threshold is VDD/2





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VDD	Operating Voltage		3.0	3.3	3.6	V
V <sub>IH</sub>	Input High Voltage	CLK <sup>(1)</sup>	2.1		3.6	V
V <sub>IL</sub>	Input Low Voltage	CLK <sup>(1)</sup>			0.7	V
I	Input High Current	CLK <sup>(1)</sup>			85	μΑ
I	Input Low Current	CLK <sup>(1)</sup>			1	μΑ
I <sub>IH</sub>	Input High Current	OE <sup>(1)</sup>			1	μΑ
I	Input Low Current	OE <sup>(1)</sup>			85	μΑ
V <sub>oh</sub>	Output High Voltage	$I_{OH} = -8mA$	2.8			V
V <sub>ol</sub>	Output Low Voltage	$I_{OL} = 8mA$			0.2	V
IDD	Operating Supply Current	No load, 133 MHz			21	mA
Z <sub>o</sub>	Nominal Output Impedance			20		Ω
C <sub>IN</sub>	Input Capacitance	CLK, OE pin		5		pF
I <sub>os</sub>	Short Circuit Current			±50		mA

### VDD=3.3 V ±10%, Ambient temperature -40 to +85° C, unless stated otherwise

Notes: 1. Nominal switching threshold is VDD/2

## **AC ELECTRICAL CHARACTERISTICS**

VDD=1.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
F <sub>OUT</sub>	Output Frequency		0		166	MHz
tOR	Output Rise Time	20% to 80%		1.0	1.5	ns
tOF	Output Fall Time	20% to 80%		1.0	1.5	ns
T <sub>PD</sub>	Propagation Delay (Note1)		2	3	5	ns
T <sub>sk</sub>	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps

<b>VDD=1.8 V ±5%,</b> Ambient temperature -40 to +85° C, unless stated otherwise
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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
F <sub>OUT</sub>	Output Frequency		0		166	MHz
tOR	Output Rise Time	20% to 80%		1.0	1.5	ns
tOF	Output Fall Time	20% to 80%		1.0	1.5	ns
T <sub>PD</sub>	Propagation Delay <sup>(1)</sup>		1.3	2	4	ns
Т <sub>sk</sub>	Output to Output Skew <sup>(2)</sup>	Rising edges at VDD/2		0	±250	ps
J <sub>ADD</sub>	Additive Jitter	@156.25MHz, 12k to 20MHz		0.1		ps





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
F <sub>OUT</sub>	Output Frequency		0		200	MHz
tOR	Output Rise Time	20% TO 80%		1.0	1.5	ns
tOF	Output Fall Time	20% TO 80%		1.0	1.5	ns
T <sub>PD</sub>	Propagation Delay <sup>(1)</sup>		0.8	1.5	3	ns
T <sub>sk</sub>	Output to Output Skew <sup>(2)</sup>	Rising edges at VDD/2		0	±250	ps
J <sub>ADD</sub>	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

#### VDD=2.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Notes:

1. With rail to rail input clock

2. Between any 2 outputs with equal loading.

### VDD=3.3 V ±10%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
F <sub>out</sub>	Output Frequency		0		200	MHz
tOR	Output Rise Time	20% TO 80%		1.0	1.5	ns
tOF	Output Fall Time	20% TO 80%		1.0	1.5	ns
T <sub>PD</sub>	Propagation Delay (Note1)		0.8	1.0	2.5	ns
T <sub>sk</sub>	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J <sub>ADD</sub>	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

Notes:

1. With rail to rail input clock

2. Between any 2 outputs with equal loading.

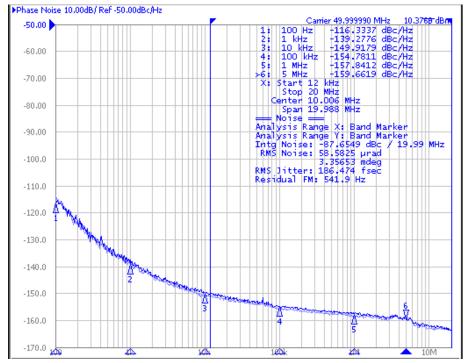
# **Thermal Characteristics**

Symbol	Parameter	Тур.	Units
θЈА	Thermal Resistance Junction to Ambient	157	°C/W
өјС	Thermal Resistance Junction to Case	42	°C/W





### **Phase Noise Plot**







# **Application Information** Suggest for Unused Inputs and Outputs

### **LVCMOS Input Control Pins**

It is suggested to add pull-up=4.7k and pull-down=1k for LVCMOS pins even though they have internal pull-up/down but with much higher value (>=50k) for higher design reliability.

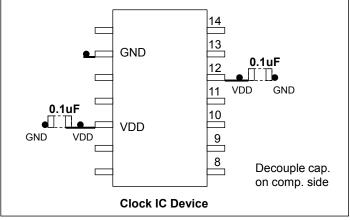
### Outputs

All unused outputs are suggested to be left open and not connected to any trace. This can lower the IC power consumption.

# **Power Decoupling & Routing**

### **VDD Pin Decoupling**

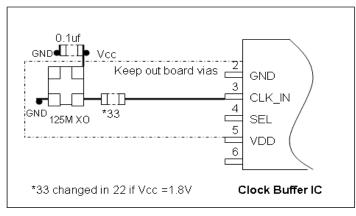
Each VDD pin must have a 0.1uF decoupling capacitor. For better decoupling, 1uF can be used. Locating the decoupling capacitor on the component side has better decoupling filter result as shown.



Placement of Decoupling caps

### **CMOS Clock Trace Routing**

Please ensure that there is a sufficient keep-out area to the adjacent trace (>20mil.). In an example using a 125MHz XO driving a buffer IC, it is better to route the clock trace on the component side with a 33 ohm termination resistor.



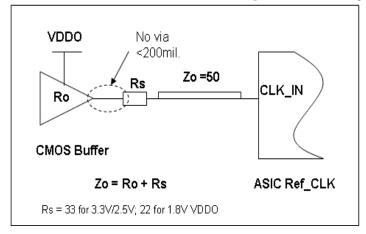




# **CMOS Output Termination**

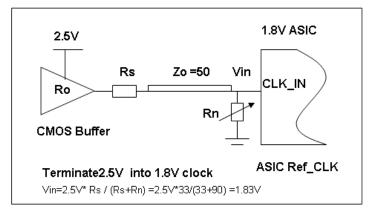
### **Popular CMOS Output Termination**

The most popular CMOS termination is a serial resitor close to the output pin (<=200mil). It is simple and balances the drive strength. The resistor's value can be fine tuned for best performance during board bring-up based on VDDO voltage used.



### **Combining Serial and Parallel Termination**

Designers can also use a parallel termination for CMOS outputs. For example, a 50 ohm pull-down resistor can be used at the Rx side to reduce signal reflection, but it reduces the signals V\_swing in half. This pull-down can be combined with a serial resitor to form a smaller clock voltage difference. The following diagram shows how to transition a 2.5V clock into 1.8V clock.



 $Rs = 33\Omega$  with  $Rn = 100\Omega$  to transition 3.3V CMOS to 2.5V Rs=  $43\Omega$  with Rn =70 $\Omega$  to transition 3.3V CMOS to 1.8V



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PI6C49X0204C

#### **Clock Jitter Definitions**

#### Total jitter= RJ + DJ

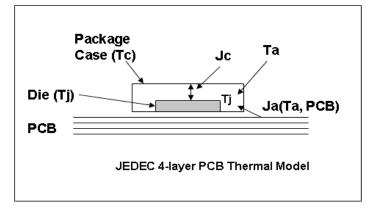
Random Jitter (RJ) is an unpredictable and unbounded timing noise that can fit in a Gaussian math distribution in RMS. RJ test values are directly related with how long or how many test samples are available. Deterministic Jitter (DJ) is timing jitter that is predictable and periodic in a fixed interference frequency. Total Jitter (TJ) is the combination of random jitter and deterministic jitter, where TJ is a factor based on total test sample count. JEDEC std. specifies digital clock TJ in 10k random samples.

#### Phase Jitter

Phase noise is short-term random noise attached on the clock carrier and is a function of the clock offset from the carrier; for example, dBc/Hz@10kHz, which is phase noise power in 1-Hz normalized bandwidth, vs. the carrier power @10kHz offset. Integration of phase noise in plot over a given frequency band yields RMS phase jitter; for example, to specify phase jitter <=1ps at 12k to 20MHz offset band as SONET standard specification.

### **Device Thermal Calculation**

The JEDEC thermal model in a 4-layer PCB is shown below.



JEDEC IC Thermal Model

Important factors to influence device operating temperature are:

1) The power dissipation from the chip (P\_chip) is after subtracting power dissipation from external loads. Generally it can be the no-load device Idd

2) Package type and PCB stack-up structure, for example, 1oz 4 layer board. PCB with more layers and are thicker ha better heat dissipation

3) Chassis air flow and cooling mechanism. More air flow M/s and adding heat sink on device can reduce device final die junction temperature Tj

The individual device thermal calculation formula:

### Tj =Ta + Pchip x Ja

### Tc = Tj - Pchip x Jc

Ja \_\_\_\_ Package thermal resistance from die to the ambient air in C/W unit; This data is provided in JEDEC model simulation. An air flow of 1m/s will reduce Ja (still air) by 20~30%

Jc \_\_\_\_ Package thermal resistance from die to the package case in C/W unit

- Tj \_\_\_\_ Die junction temperature in C (industry limit <125C max.)
- Ta \_\_\_\_ Ambient air temperature in °C
- Tc \_\_\_\_ Package case temperature in °C

Pchip\_\_\_ IC actually consumes power through Iee/GND current





# **Part Marking**

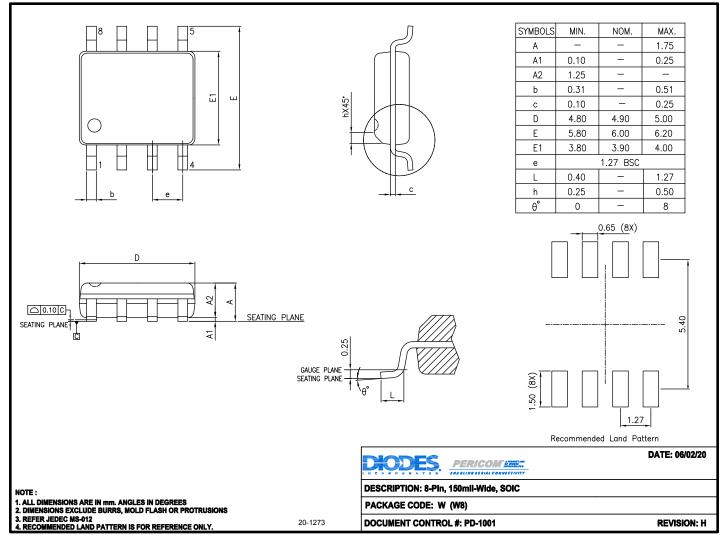


YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code





# Packaging Mechanical: 8-SOIC (W)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

## **Ordering Information**

Ordering Code	Package Code	Package Description
PI6C49X0204CWIEX	W	8-pin, 150mil-Wide SOIC

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm

antimony compounds. 4. E = Pb-free and Green

5. X suffix = Tape/Reel





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